

N-channel SiC power MOSFET

V_{DSS}	650V
R _{DS(on)} (Typ.)	$60 {\sf m}\Omega$
I _D	39A
P_D	165W

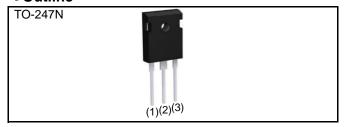
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

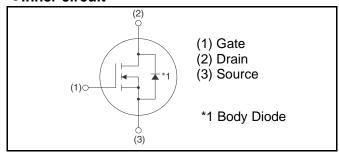
Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

Outline



●Inner circuit



Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Type Basic ordering	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT3060AL

◆Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{ extsf{DSS}}$	650	V	
Continuous drain current	T _c = 25°C	I _D *1	39	А
Continuous arain current	T _c = 100°C	I _D *1	27	А
Pulsed drain current	I _{D,pulse} *2	97	А	
Gate - Source voltage		V_{GSS}	-4 to 22	V
Gate-Source Surge Voltage		V_{GSS_surge}	−4 to 22	V
Recommended Drive Voltage		V_{GS_op}	0 / 18	V
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

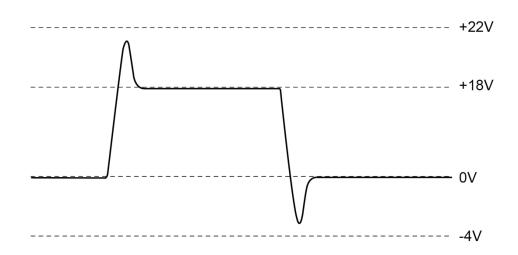
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC}	-	0.70	0.91	°C/W

•Electrical characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol	Conditions	Values			Unit
	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	650	-	-	V
		$V_{DS} = 650V, V_{GS} = 0V$				
Zero gate voltage drain current	I _{DSS}	$T_j = 25$ °C	-	1	10	μΑ
didiii odiioiit		T _j = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS} _	$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_D = 6.67 \text{mA}$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 13A$				
Static drain - source on - state resistance	R _{DS(on)} *3	T _j = 25°C	-	60	78	mΩ
2 2.3.0 .00.0.00		T _j = 125°C	-	79.2	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	12	-	Ω

●Example of acceptable Vgs waveform



●Electrical characteristics (T_a = 25°C)

Parameter	Cumbal	Symbol Conditions		Values		
	Conditions	Min.	Тур.	Max.	Unit	
Transconductance	g fs *3	$V_{DS} = 10V, I_D = 13A$	-	4.9	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	852	-	
Output capacitance	C _{oss}	V _{DS} = 500V	-	55	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	24	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 300V	-	126	-	pF
Turn - on delay time	t _{d(on)} *3	$V_{DD} = 300V, I_D = 13A$	-	19	-	
Rise time	t _r *3	$V_{GS} = 18V/0V$	-	37	-	no
Turn - off delay time	t _{d(off)} *3	$R_L = 23\Omega$	-	34	-	ns
Fall time	t _f *3	$R_G = 0\Omega$	-	21	-	
Turn - on switching loss	E _{on} *3	$V_{DD} = 300V, I_{D} = 13A$ $V_{GS} = 18V/0V$	-	70		
Turn - off switching loss	E _{off} *3	R _G = 0Ω L=500μH *E _{on} includes diode reverse recovery	-	10	1	μJ

•Gate Charge characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*3}	V _{DD} = 300V	-	58	-	
Gate - Source charge	Q _{gs} *3	I _D = 13A	-	15	-	nC
Gate - Drain charge	Q _{gd} *3	V _{GS} = 18V	-	23	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 300V, I_D = 13A$	-	9.6	,	V

^{*1} Limited only by maximum temperature allowed.

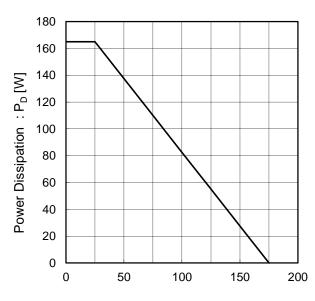
^{*2} PW \leq 10 $\mu s,$ Duty cycle \leq 1%

^{*3} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

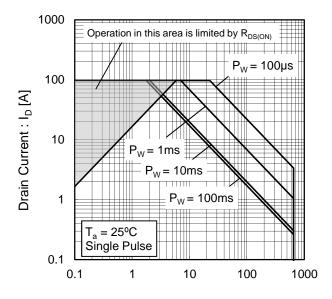
Parameter	Cymbol	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	1	39	А
Inverse diode direct current, pulsed	I _{SM} *2		-	-	97	Α
Forward voltage	V_{SD}^{*3}	$V_{GS} = 0V, I_{S} = 13A$	-	3.2	-	V
Reverse recovery time	t _{rr} *3	I _F = 13A, V _R = 300V di/dt = 1100A/μs	-	15	1	ns
Reverse recovery charge	Q _{rr} *3		-	55		nC
Peak reverse recovery current	I _{rrm} *3		-	8	-	Α

Fig.1 Power Dissipation Derating Curve



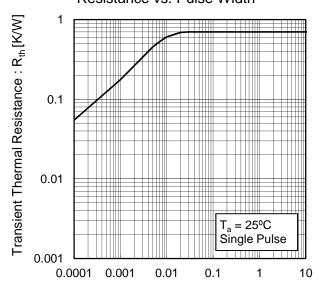
Junction Temperature : T_i [°C]

Fig.2 Maximum Safe Operating Area



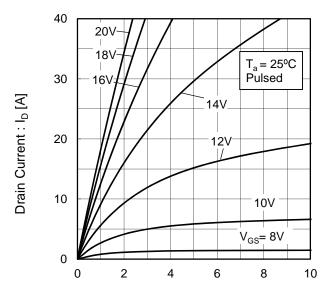
Drain - Source Voltage : V_{DS} [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



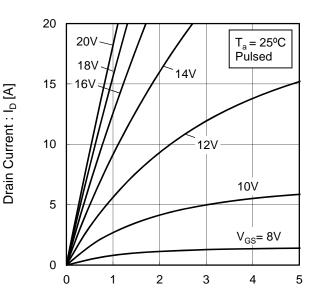
Pulse Width : P_W [s]

Fig.4 Typical Output Characteristics(I)

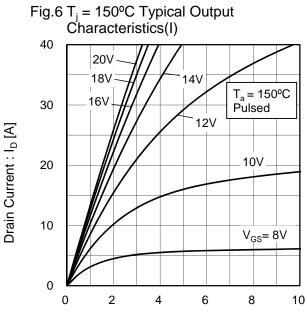


Drain - Source Voltage : V_{DS} [V]

Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

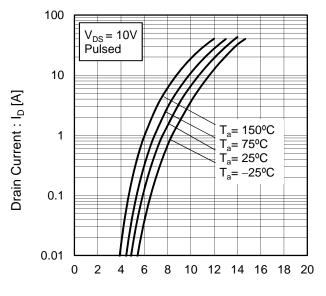


Drain - Source Voltage : V_{DS} [V]

Fig.7 $T_j = 150^{\circ}C$ Typical Output Characteristics(II) 20 20V 18V 16V 10V 15 12V Drain Current: I_D [A] 10 V_{GS}= 8V 5 $T_a = 150^{\circ}C$ Pulsed 2 3 5 0

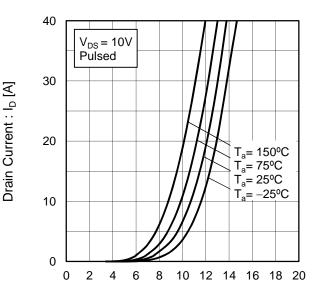
Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Transfer Characteristics (I)



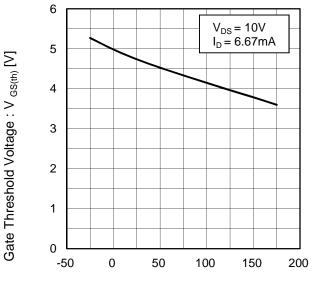
Gate - Source Voltage : V_{GS} [V]

Fig.9 Typical Transfer Characteristics (II)



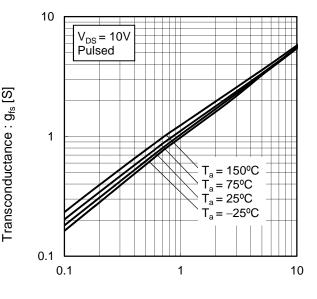
Gate - Source Voltage : V_{GS} [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.11 Transconductance vs. Drain Current



Drain Current : I_D [A]

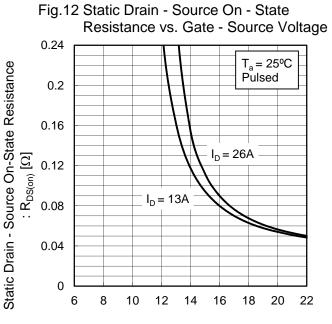
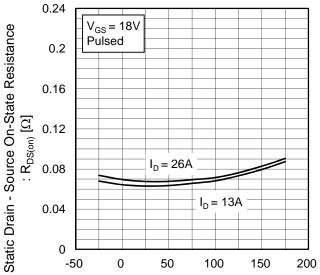


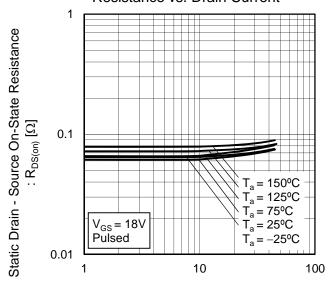
Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current

Gate - Source Voltage : V_{GS} [V]



Drain Current: I_D [A]

Fig.15 Typical Capacitance vs. Drain - Source Voltage 10000 1000 Capacitance: C [pF] Coss 100 10 $T_a = 25^{\circ}C$ f = 1MHz $t_{GS} = 0V$ 1

Drain - Source Voltage : V_{DS} [V]

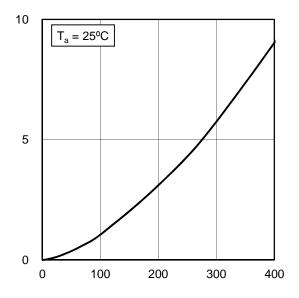
100

1000

10

Fig.16 Coss Stored Energy

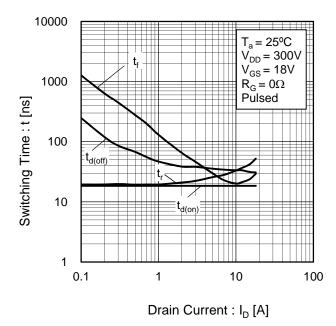
Coss Stored Energy : E_{OSS} [μJ]



Drain - Source Voltage : V_{DS} [V]

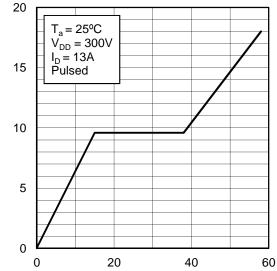
Fig.17 Switching Characteristics

0.1



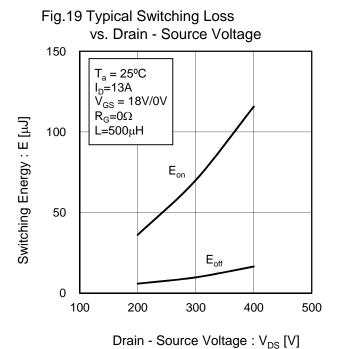
20

Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q_g [nC]

3ate - Source Voltage: V_{GS} [V]



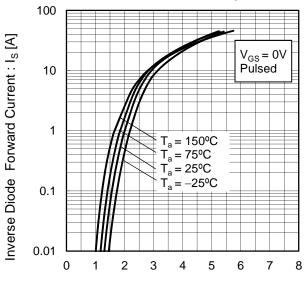
vs. Drain Current 600 $T_a = 25^{\circ}C$ $V_{DD} = 300V$ $V_{GS} = 18V/0V$ $R_{G} = 0\Omega$ Switching Energy: E [µJ] L=500μH 400 E_{on} 200 $\mathsf{E}_{\mathsf{off}}$ 0 0 20 40 Drain Current: I_D [A]

Fig.20 Typical Switching Loss

Fig.21 Typical Switching Loss vs. External Gate Resistance 600 $T_a = 25^{\circ}C$ V_{DD}=300V $I_D = 13A$ $V_{GS} = 18V/0V$ L=500 μ H 400 Eon 200 E_{off} 0 5 10 15 20 25

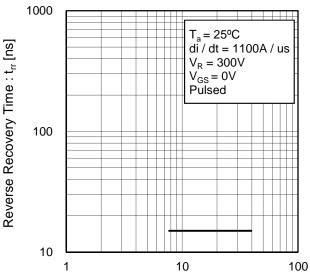
External Gate Resistance : $R_G[\Omega]$

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

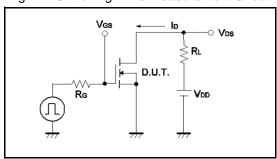


Fig.2-1 Gate Charge Measurement Circuit

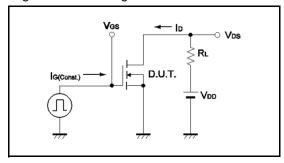


Fig.3-1 Switching Energy Measurement Circuit

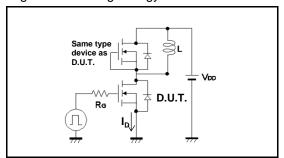


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

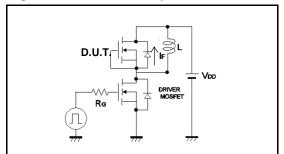


Fig.1-2 Switching Waveforms

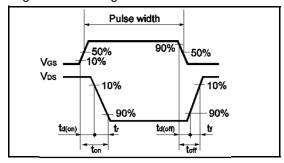


Fig.2-2 Gate Charge Waveform

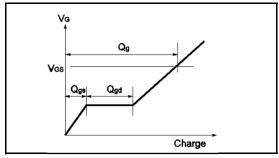
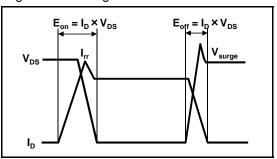
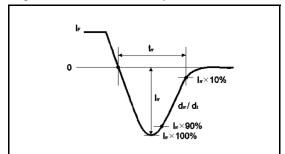


Fig.3-2 Switching Waveforms





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SCT3060AL - Web Page

Distribution Inventory

Part Number	SCT3060AL
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes